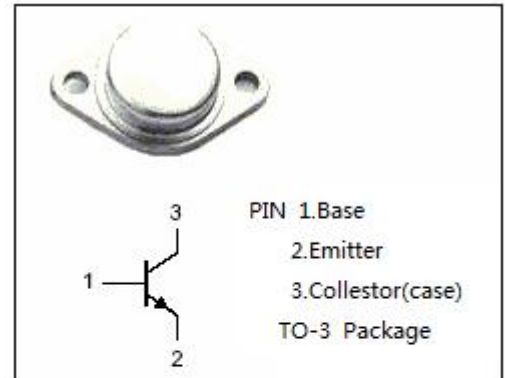


**DESCRIPTION**

- High DC Current Gain- $h_{FE}=15\sim60@I_C = 25A$
- Low Saturation Voltage-  
 $V_{CE(sat)}= 1.0V(Max)@ I_C = 25A$

**APPLICATIONS**

- Designed for use in high power amplifier and switching circuits applications.

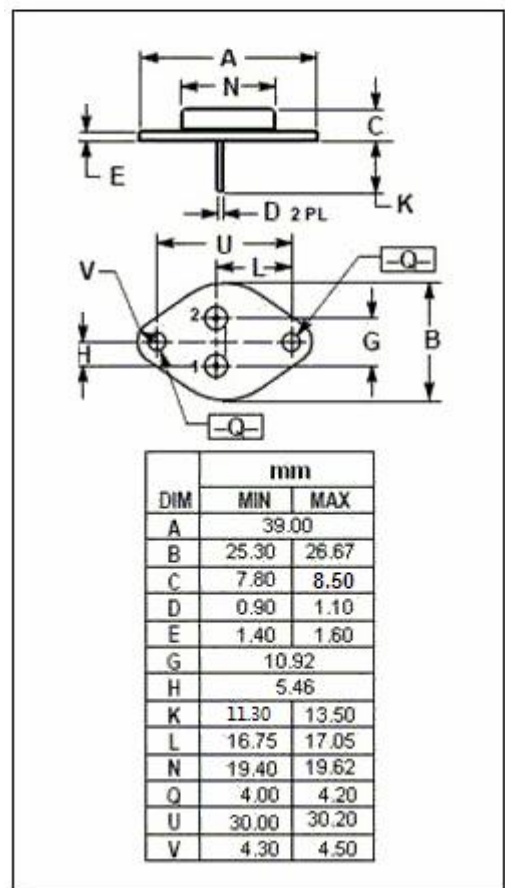


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	50	A
$I_B$	Base Current-Continuous	15	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	300	W
$T_J$	Junction Temperature	200	$^\circ C$
$T_{stg}$	Storage Temperature	-65~200	$^\circ C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.584	$^\circ C/W$



**ELECTRICAL CHARACTERISTICS**

$T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CE0(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=50\text{mA}$ ; $I_B=0$	80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C= 25\text{A}$ ; $I_B=2.5\text{A}$		1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C= 50\text{A}$ ; $I_B=10\text{A}$		5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 25\text{A}$ ; $I_B=2.5\text{A}$		2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C= 25\text{A}$ ; $V_{CE}=2\text{V}$		2.0	V
$I_{CEO}$	Collector Cutoff Current	$V_{CE}=40\text{V}$ ; $I_B=0$		1	mA
$I_{CBO}$	Collector Cutoff Current	$V_{CB}= 80\text{V}$ ; $I_C=0$		2	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}= 5\text{V}$ ; $I_C=0$		5	mA
$h_{FE-1}$	DC Current Gain	$I_C= 25\text{A}$ ; $V_{CE}= 2\text{V}$	15	60	
$h_{FE-2}$	DC Current Gain	$I_C= 50\text{A}$ ; $V_{CE}= 5\text{V}$	5		
$f_T$	Current Gain-Bandwidth Product	$I_C= 5\text{A}$ ; $V_{CE}= 10\text{V}$ ; $f=1.0\text{MHz}$	2		MHz